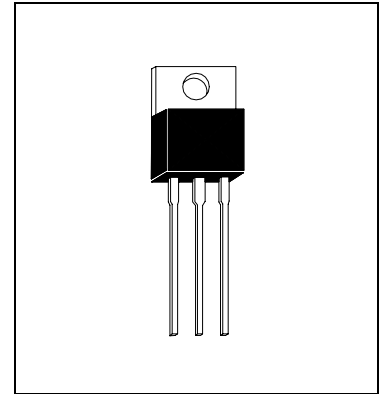




HSK1118

Description

- Field Effect Transistor.
- Silicon N Channel MOS Type.
- High Speed, High Current DC-DC Converter, Relay Drive and Motor Drive Applications



Features

- 4-Volt Gate Drive
- Low Drain-Source On Resistance - $R_{DS(on)}=0.95\Omega$ (Typ.)
- High Forward Transfer Admittance - $|Y_{fs}|=4.0S$ (Typ.)
- Low Leakage Current - $I_{DSS} = 300\mu A$ (Max.) @ $V_{DS} = 600V$
- Enhancement-Mode - $V_{th} = 1.5\sim 3.5V$ @ $V_{DS} = 10V, I_D = 1mA$

Absolute Maximum Ratings (Ta=25°C)

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature 150 °C
- Maximum Power Dissipation
 - Total Power Dissipation (Tc=25°C) 45 W
- Maximum Voltages and Currents (Tc=25°C)
 - DRAIN to SOURCE Breakdown Voltage 600 V
 - DRAIN to GATE Breakdown Voltage 600 V
 - GATE to SOURCE Voltage ±30 V
 - DRAIN Current (Cont.)..... 6 A
 - DRAIN Current (Pluse) 24 A

Thermal Characteristics

Characteristic	Symbol	Max.	Units
Junction to Case	RθJC	2.77	°C/W
Junction to Ambient	RθJA	62.5	°C/W

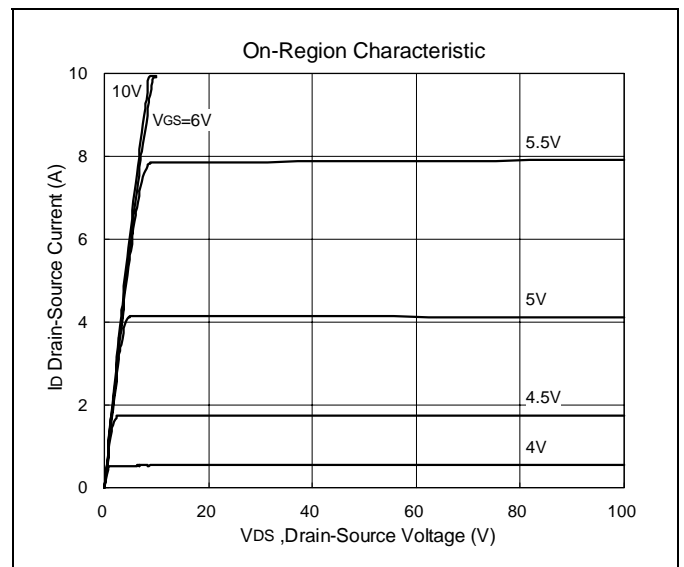
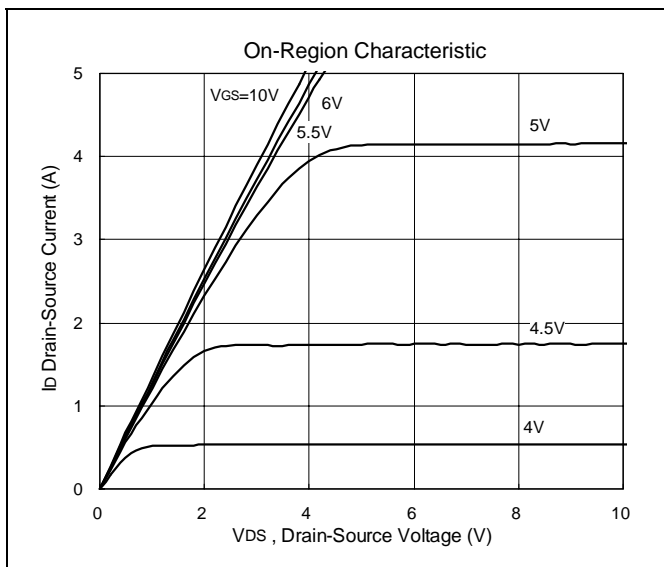
Note : This transistor is an electrostatic sensitive device. Please handle with care.

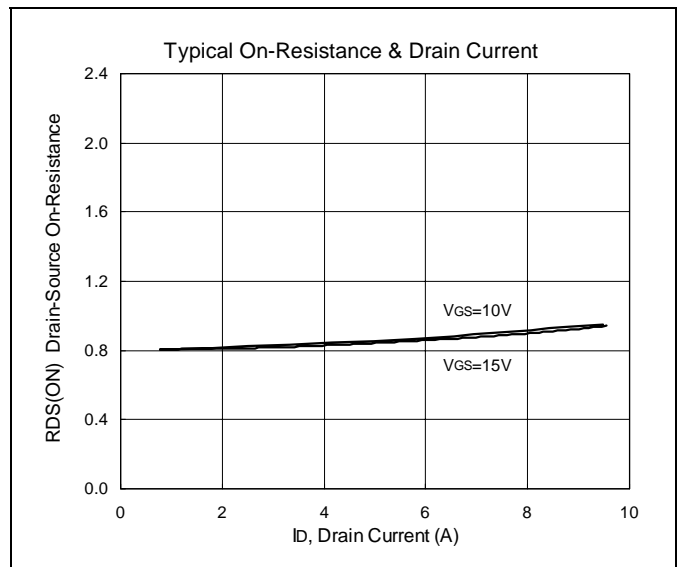
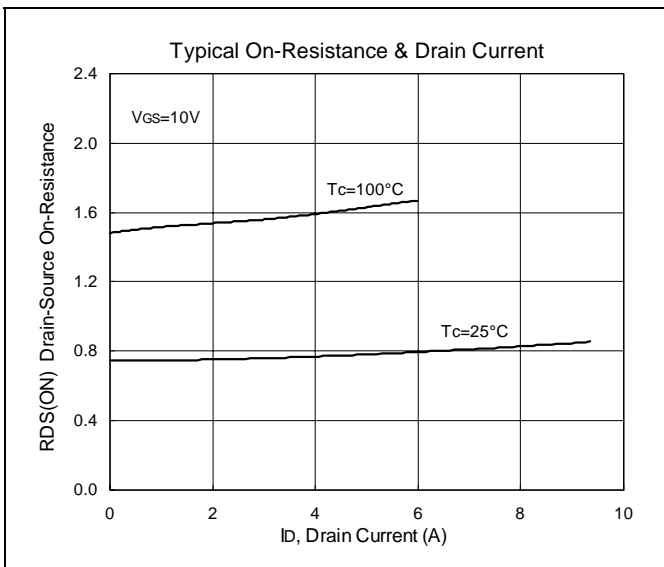
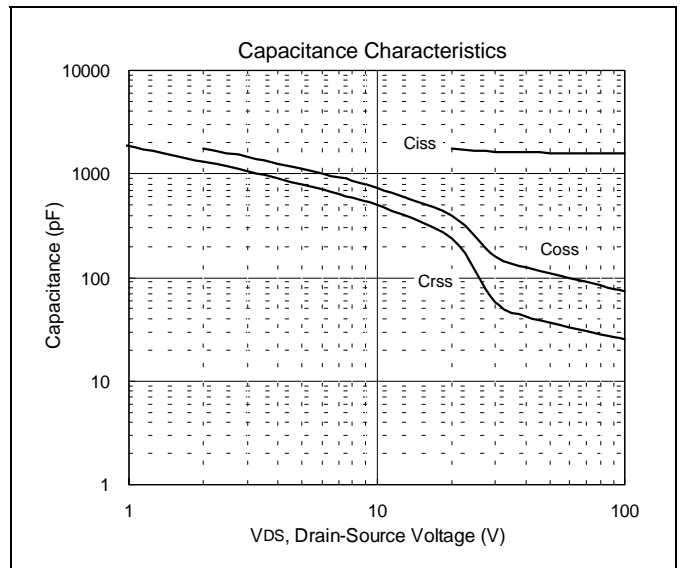
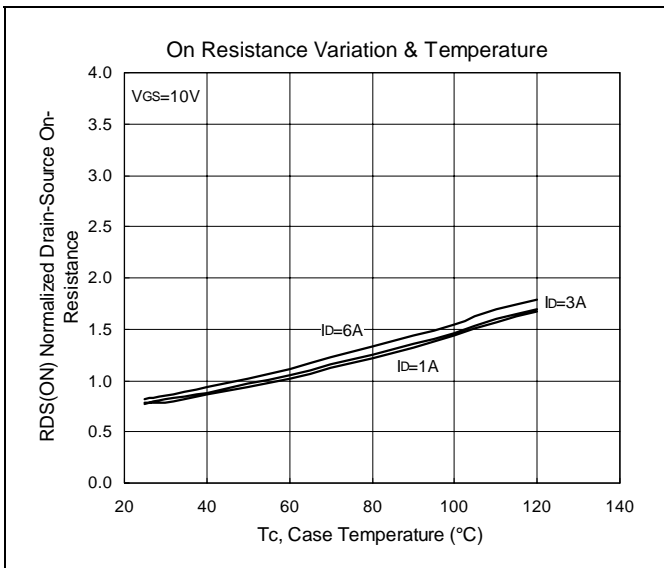
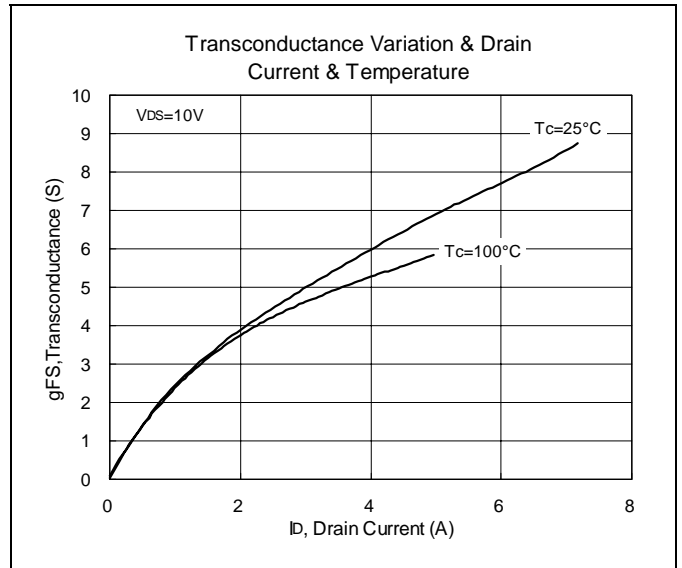
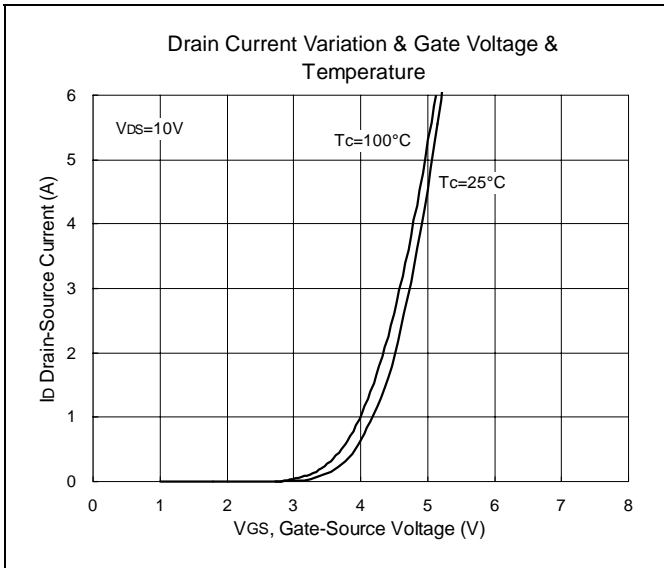


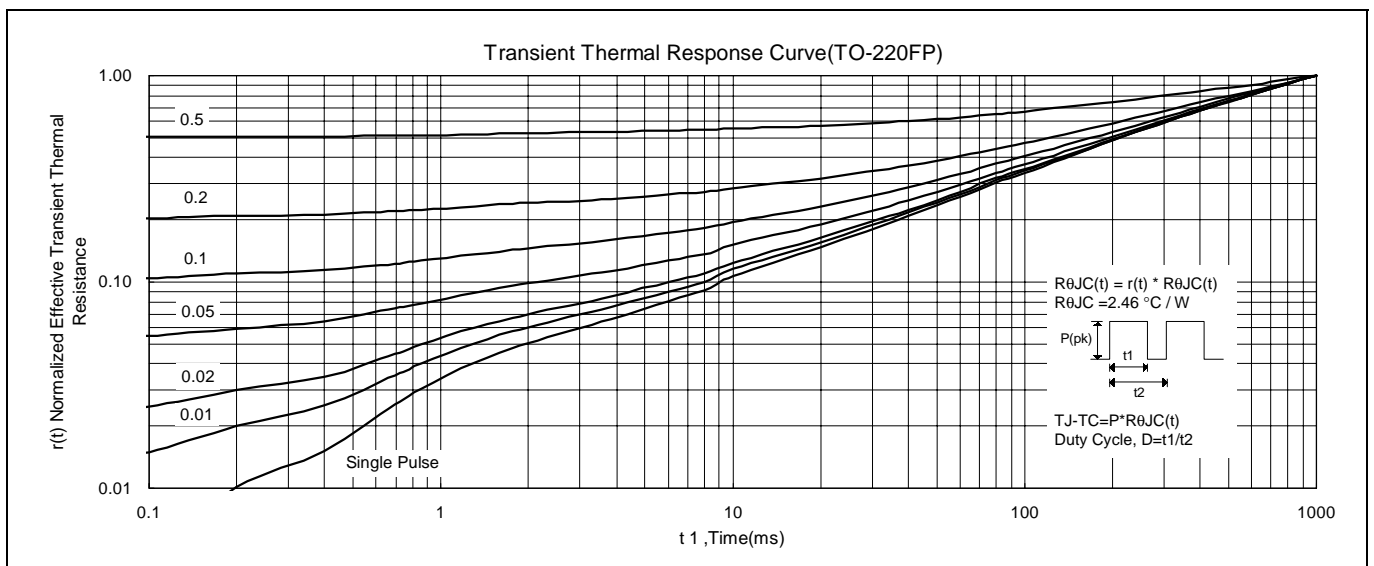
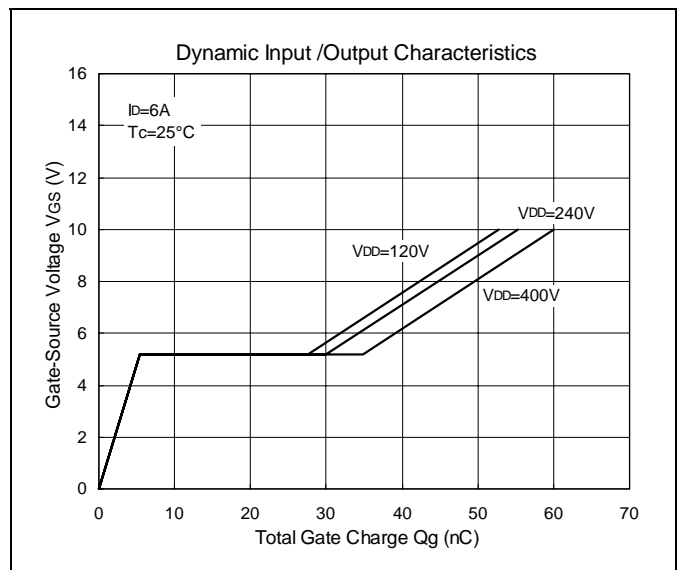
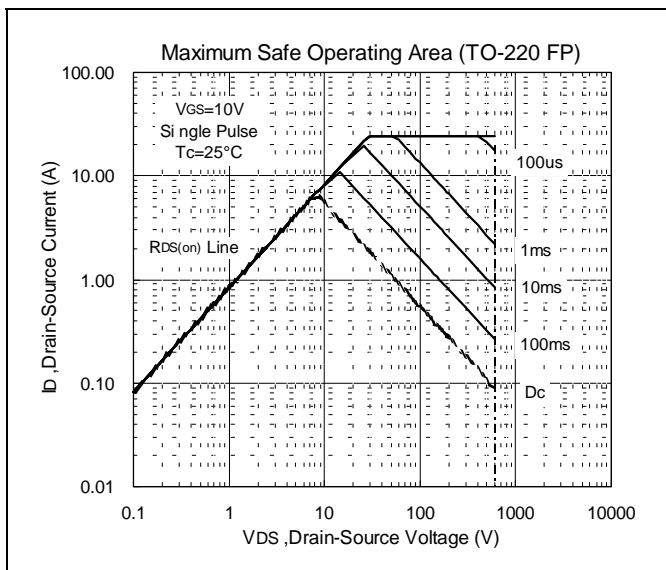
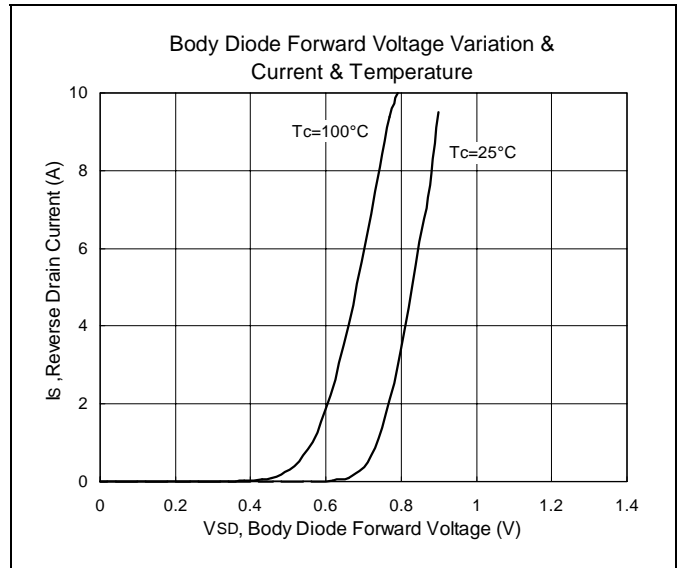
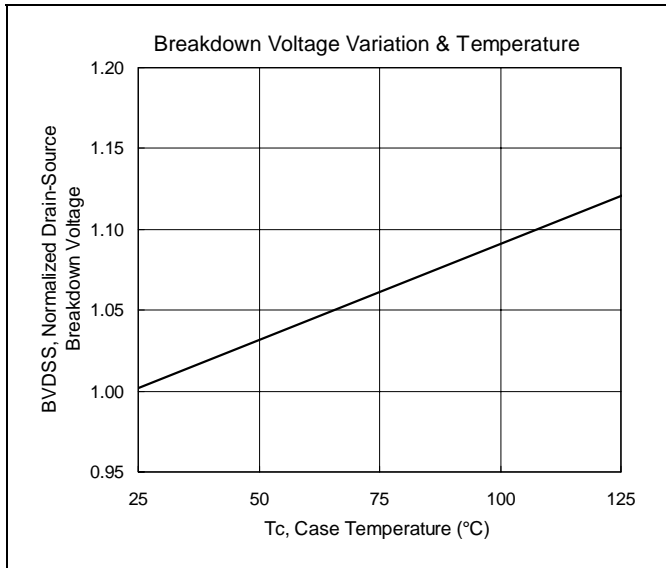
Characteristics (Ta=25°C)

Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	600	-	-	V	$I_D=250\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	2	-	4	V	$V_{DS}=10V, I_D=1mA$
Drain Cut-Off Current	I_{DSS}	-	-	25	μA	$V_{DS}=600V$
Gate Leakage Current	I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 25V$
Drain-Source On Voltage	$V_{DS(ON)}$	-	-	6	V	$I_D=5.0A, V_G=10V$
On-State Drain Current	$I_{D(ON)}$	9	-	-	A	$V_{DS}=10V, V_{GS}=10V$
Drain-Source ON Resistance	$R_{DS(ON)}$	-	0.95	1.25	Ω	$V_{GS}=10V, I_D=3A$
Input Capacitance	C_{iss}	-	2000	-	pF	$V_{DS}=10V, V_{GS}=0V$ $f=1MHz$
Reverse Transfer Capacitance	C_{rss}	-	500	-	pF	
Output Capacitance	C_{oss}	-	740	-	pF	
Switching Time	T_r	-	50	-	nS	$V_{IN} : T_r, T_f < 5nS$ $V_{DD}=300V, I_D=3A$ $V_{GS}=10V$ Duty $\leq 1\%$, $t_w=10\mu S$
	T_{on}	-	80	-		
	T_f	-	40	-		
	T_{off}	-	170	-		
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	-	60	-	nC	$I_D=6A$ $V_{DS}=400V$ $V_{GS}=10V$
Gate-Source Charge	Q_{gs}	-	30	-	nC	
Gate-Drain Charge (Miller)	Q_{gd}	-	30	-	nC	

Characteristics Curve

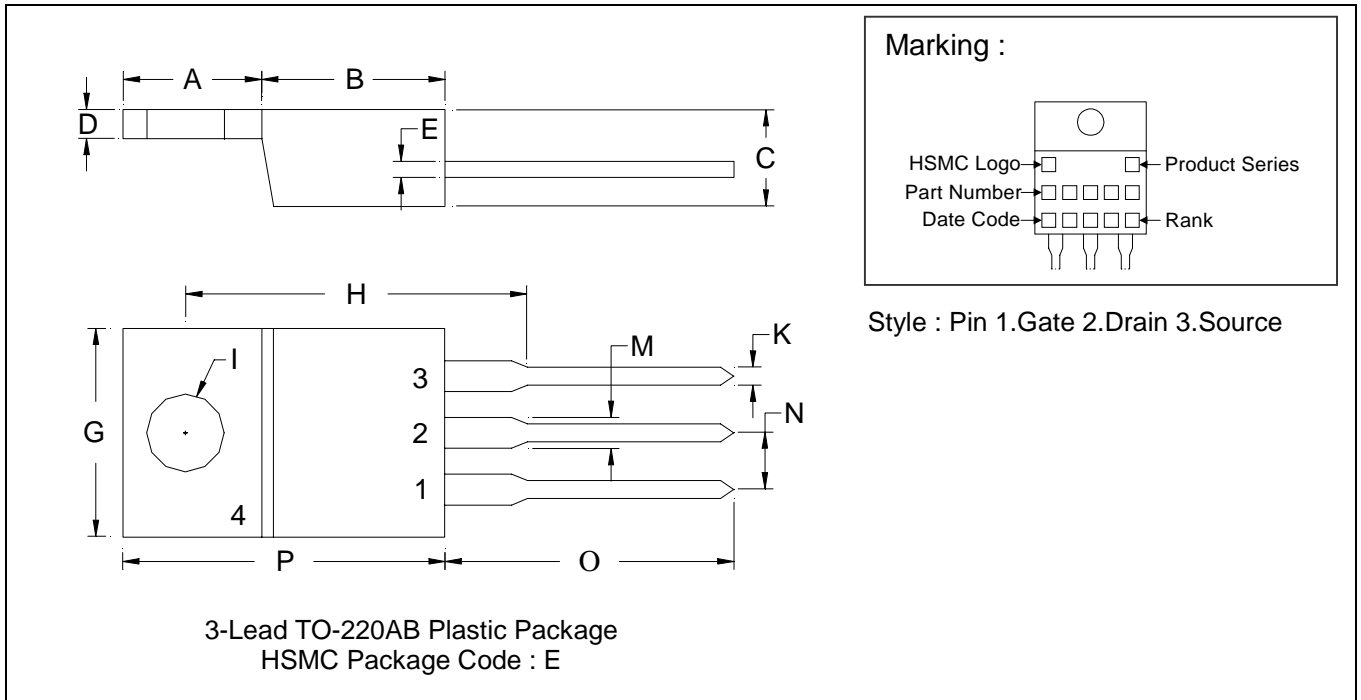








TO-220AB Dimension



*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.2197	0.2949	5.58	7.49	I	-	*0.1508	-	*3.83
B	0.3299	0.3504	8.38	8.90	K	0.0295	0.0374	0.75	0.95
C	0.1732	0.185	4.40	4.70	M	0.0449	0.0551	1.14	1.40
D	0.0453	0.0547	1.15	1.39	N	-	*0.1000	-	*2.54
E	0.0138	0.0236	0.35	0.60	O	0.5000	0.5618	12.70	14.27
G	0.3803	0.4047	9.66	10.28	P	0.5701	0.6248	14.48	15.87
H	-	*0.6398	-	*16.25					

- Notes :**
- 1.Dimension and tolerance based on our Spec. dated Sep. 07,1997.
 - 2.Controlling dimension : millimeters.
 - 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material :

- Lead : 42 Alloy ; solder plating
- Mold Compound : Epoxy resin family, flammability solid burning class:UL94V-0

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